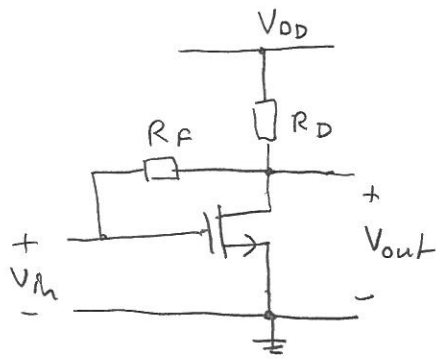


3.20 a

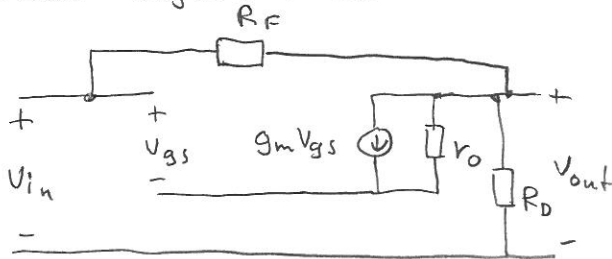
2010-01-19 / Bengt M.



Assume transistor in saturation

$$V_{DS} > V_{GS} - V_{TH}$$

Small signal model



$$\begin{cases} V_{GS} = V_{in} \\ \frac{V_{out} - V_{in}}{R_F} + \frac{V_{out}}{r_o} + \frac{V_{out}}{R_D} + g_m V_{gs} = 0 \end{cases}$$

$$V_{out} \left(\frac{1}{R_F} + \frac{1}{r_o} + \frac{1}{R_D} \right) = V_{in} \left(\frac{1}{R_F} - g_m \right)$$

$$A_V = \frac{V_{out}}{V_{in}} = - \frac{g_m - \frac{1}{R_F}}{\frac{1}{R_F} + \frac{1}{r_o} + \frac{1}{R_D}}$$

Check with values, use model in Table 2.1

Assume: Bias at input $V_{in} = 1,0 \text{ V DC}$

$$\frac{W}{L_{drawn}} = \frac{50}{0,5} \Rightarrow L_{eff} = L_{drawn} - 2L_D = 0,5 - 2 \cdot 0,08 = 0,34 \mu\text{m}$$

$$I_D = \frac{1}{2} \mu_n C_{ox} \cdot \frac{W}{L} (V_{GS} - V_{TH})^2$$

$$V_{TH} = 0,7 \text{ V}$$

$$\frac{\text{cm}^2}{V_s} \cdot \frac{F}{\text{cm}^2} = \frac{F}{V_s} = \frac{\text{As/V}}{V_s} = \frac{A}{V^2}$$

$$\mu_n = \mu_0 = 350 \frac{\text{cm}^2}{V_s}$$

$$C_{ox} = \frac{\epsilon_{ox}}{t_{ox}} = \frac{8,85 \cdot 10^{-14} \cdot 3,9 \text{ F/cm}}{9 \cdot 10^{-7} \text{ cm}} = 3,84 \text{ F/cm}^2$$

$$\mu_n C_{ox} = 350 \cdot 3,84 = 134 \text{ mA/V}^2 \quad \leftarrow$$

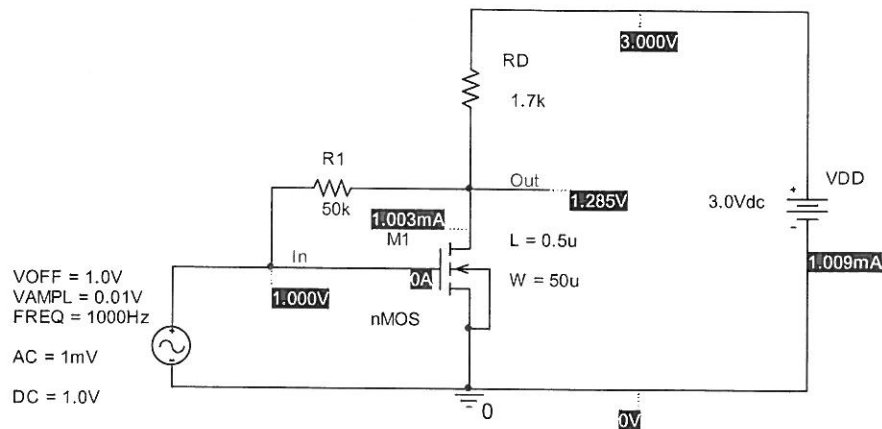
$$I_D = \frac{1}{2} \cdot 134 \mu\text{A} \cdot \frac{50 \mu\text{m}}{0,34 \mu\text{m}} (1 - 0,7)^2 = 0,88 \text{ mA}$$

Design V_{out} DC-level $\approx 1,5 \text{ V}$ and $V_{DD} = 3 \text{ V}$

$$R_D = \frac{V_{DD} - V_{DS}}{I_D} = \frac{3 - 1,5}{0,88 \text{ mA}} = \frac{1,5}{0,88 \text{ mA}} = 1,7 \text{ k}\Omega$$

$$R_F = 50 \text{ k}$$

Problem 3.2 a



From output file

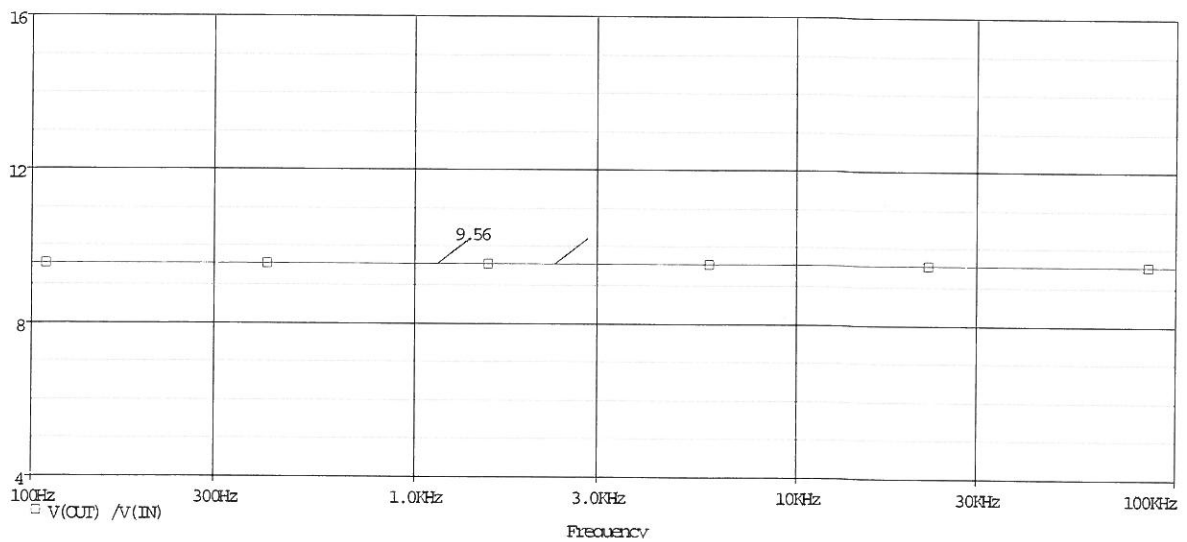
NAME	M_M1
MODEL	nMOS
ID	1.00E-03
VGS	1.00E+00
VDS	1.29E+00
VBS	0.00E+00
VTH	7.00E-01
VDSAT	3.00E-01
GM	6.69E-03
GDS	8.89E-05

DC-values
 $V_{GS} - V_{TH} = V_{OV}$

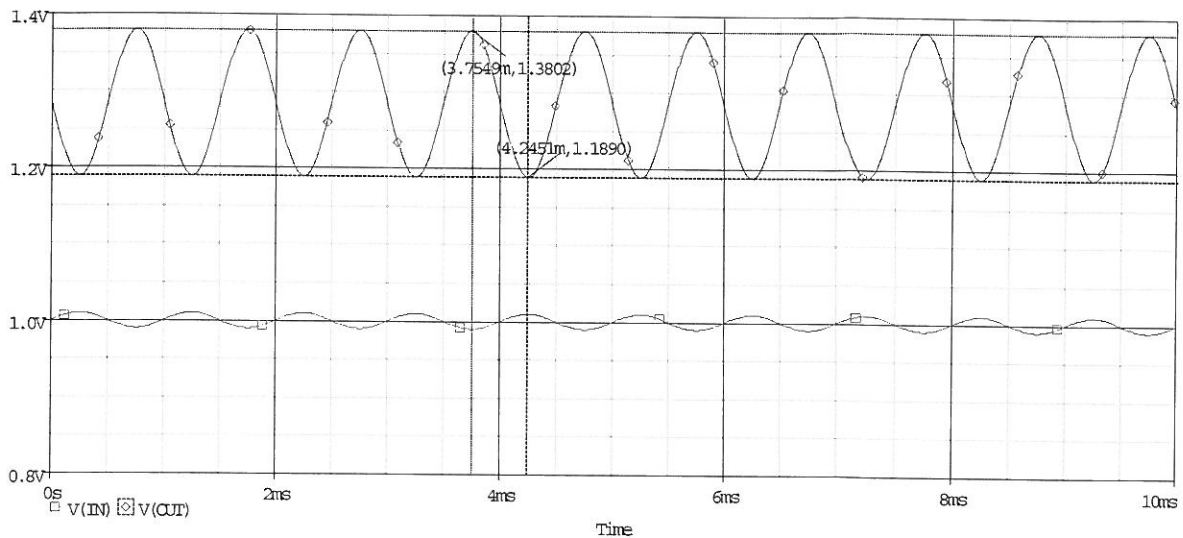
$g_m = 6,69 \text{ mA/V}$

$r_o = \frac{1}{GDS} = \frac{1}{8,89 \cdot 10^{-5}} = 11,2 \text{ k}\Omega$

AC-analysis gain = 9.56



Transient analysis 10 mV peak value input, output peak value $191.2/2 = 95.6$ mV gain = 9.56 OK!



Conclusion

Simulated DC values is higher because I have not considered channel length modulation.

$$I_D = 0,88 \text{ mA} \cdot (1 + \lambda \cdot V_{DS}) = 0,88 (1 + 0,1 \cdot 1,285) = 1,01 \text{ mA OK!}$$

Checking gain formula:

$$g_m = \frac{2I_D}{V_{GS} - V_{TH}} = \frac{2 \cdot 1,0}{0,3} = 6,67 \text{ mA/V} \quad 6.69 \text{ mA/V in simulation OK!}$$

$$r_o = \frac{1}{\lambda I_D} = \frac{1}{0,1 \cdot 1,0} = 10 \text{ k}\Omega \quad 11.2 \text{ k}\Omega \text{ from simulation}$$

$$R_F = 50 \text{ k}\Omega \quad R_D = 1,7 \text{ k}\Omega$$

$$A_V = - \frac{g_m - \frac{1}{R_F}}{\frac{1}{R_F} + \frac{1}{r_o} + \frac{1}{R_D}} = - \frac{6,69 \text{ mA/V} - \frac{1}{50 \text{ k}}}{\frac{1}{50 \text{ k}} + \frac{1}{11,2 \text{ k}} + \frac{1}{1,7 \text{ k}}} = -9.56$$

This is exactly the same result as in simulation.

The gain formula seem to be correct!